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## Determination of the Excess Charge Carrier Lifetime in Antimony Based Semiconductor Thin Films

Steady state photo-conductivity measurements are used for the determination of the lifetime of excess charge carriers in antimony based semiconductor (i.e. Ga Sb) thin films. The spectral dependence of the lifetime, as well as the dependence of lifetime on the incident photon flux density, the temperature and the doping level is investigated. In order to evaluate the surface and bulk contributions to the lifetime, samples of different thicknesses, grown under the same conditions, are analyzed.

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